Amplifier Transistors

NPN Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	75	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

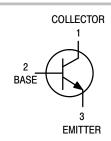
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

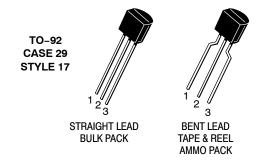
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
P2N2222AG	TO-92 (Pb-Free)	5000 Units/Bulk
P2N2222ARL1G	TO-92 (Pb-Free)	2000/Tape & Ammo

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}\text{C unless otherwise noted})$

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		1		
Collector - Emitter Breakdown Voltage	V _{(BR)CEO}			Vdc
$(I_C = 10 \text{ mAdc}, I_B = 0)$	(BR)CEO	40	-	1
Collector - Base Breakdown Voltage	V _{(BR)CBO}	75		Vdc
$(I_C = 10 \mu Adc, I_E = 0)$, ,		-	
Emitter – Base Breakdown Voltage	V _{(BR)EBO}	0.0		Vdc
$(I_E = 10 \mu\text{Adc}, I_C = 0)$	_	6.0	_	
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	ICEX	_	10	nAdc
Collector Cutoff Current	lone		1 - 1	μAdc
$(V_{CB} = 60 \text{ Vdc}, I_{E} = 0)$	I _{CBO}	_	0.01	μλασ
$(V_{CB} = 60 \text{ Vdc}, I_{E} = 0, T_{A} = 150^{\circ}\text{C})$		-	10	
Emitter Cutoff Current	I _{EBO}		10	nAdc
(V _{EB} = 3.0 Vdc, I _C = 0)		_		
Collector Cutoff Current (V _{CE} = 10 V)	I _{CEO}	_	10	nAdc
Base Cutoff Current		_	10	n A da
(V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	I _{BEX}	_	20	nAdc
ON CHARACTERISTICS		1	1	
DC Current Gain	hFE			_
$(I_C = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$	VIE .	35	_	
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$		50	_	
$(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, T_A = -55^{\circ}\text{C})$		75 35	_	
$(I_C = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \text{ (Note 1)}$		100	300	
$(I_C = 150 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \text{ (Note 1)}$		50	_	
(I _C = 500 mAdc, V _{CE} = 10 Vdc) (Note 1)		40	_	
Collector - Emitter Saturation Voltage (Note 1)	V _{CE(sat)}		0.0	Vdc
(I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)		_	0.3 1.0	
Base - Emitter Saturation Voltage (Note 1)	V _{BE(sat)}			Vdc
(I _C = 150 mAdc, I _B = 15 mAdc)	• DE(Sai)	0.6	1.2	143
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$		_	2.0	
SMALL-SIGNAL CHARACTERISTICS				
Current - Gain - Bandwidth Product (Note 2)	f _T			MHz
(I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)C		300	_	
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C_{obo}	_	8.0	pF
	-	_	0.0	~F
Input Capacitance $(V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C _{ibo}	_	25	pF
Input Impedance	h _{ie}			kΩ
$(I_{C} = 1.0 \text{ mAdc}, V_{CF} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	···le	2.0	8.0	
(I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		0.25	1.25	
Voltage Feedback Ratio	h _{re}		0.0	X 10 ⁻⁴
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$ $(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$		_	8.0 4.0	
Small-Signal Current Gain	h _{fe}			_
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	' 'te	50	300	
$(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$		75	375	
Output Admittance	h _{oe}			μMhos
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$		5.0 25	35 200	
(I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	1.00	20	200	
Collector Base Time Constant ($I_E = 20 \text{ mAdc}$, $V_{CB} = 20 \text{ Vdc}$, $f = 31.8 \text{ MHz}$)	rb′C _c	_	150	ps
Noise Figure	NI_			dB
(I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	N _F	_	4.0	ub
1 Dulas Tast: Dulas Width < 200 up Duty Cycle < 2.00/		I	1	L

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%. 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

	Symbol	Min	Max	Unit	
SWITCHING CHARACTERISTICS					
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -2.0 \text{ Vdc},$	t _d	-	10	ns
Rise Time	$I_C = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc}) \text{ (Figure 1)}$	t _r	-	25	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_C = 150 \text{ mAdc},$	t _s	-	225	ns
Fall Time	I _{B1} = I _{B2} = 15 mAdc) (Figure 2)	t _f	_	60	ns

SWITCHING TIME EQUIVALENT TEST CIRCUITS

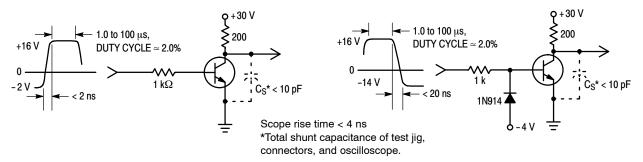


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

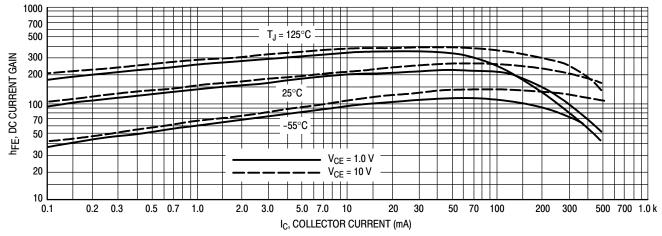


Figure 3. DC Current Gain

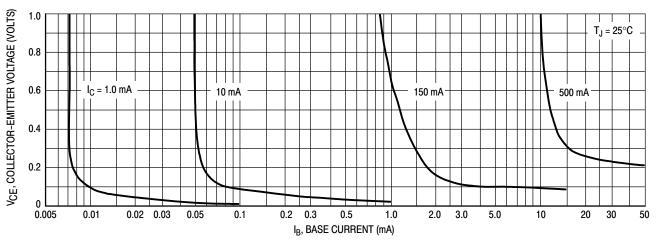


Figure 4. Collector Saturation Region

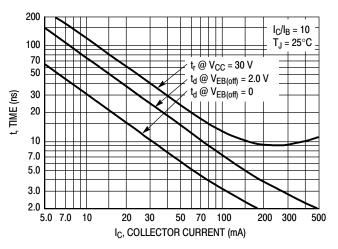


Figure 5. Turn-On Time

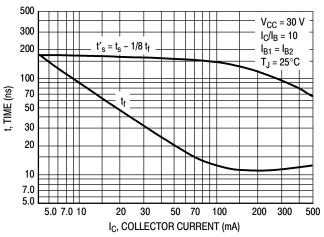


Figure 6. Turn-Off Time

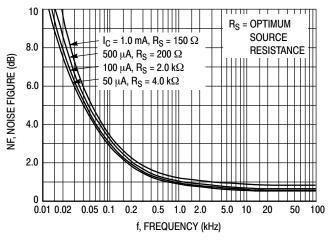


Figure 7. Frequency Effects

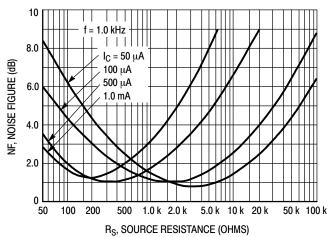


Figure 8. Source Resistance Effects

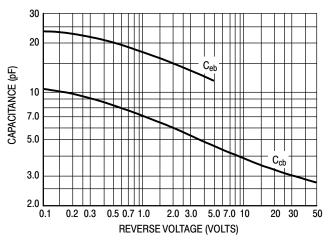
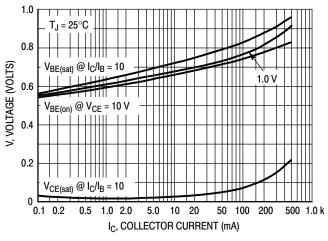


Figure 9. Capacitances

Figure 10. Current-Gain Bandwidth Product



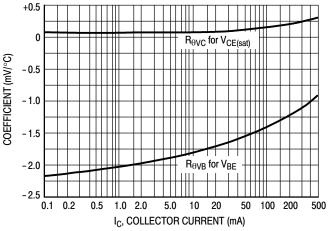
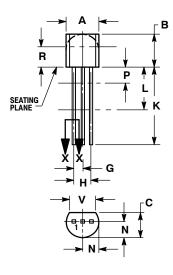


Figure 11. "On" Voltages

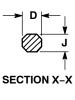
Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**

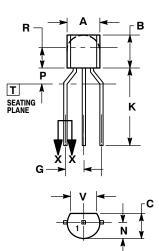


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P	-	0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- ASME Y14-3M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
 DIMENSION R IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P
 AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN MAX		
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 17:

PIN 1. COLLECTOR

BASE

EMITTER

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